

*1 cont*  
monocrystalline material layer selected from the group consisting of GaAs, GaInAs, AlGaAs, Si and AlAs, and wherein said first monocrystalline material layer has a thickness in the range of from about 20 angstroms to about 50 angstroms.

---

Please cancel Claims 3, 16 and 17-42.

Please add new Claim 43 as follows:

---

*a<sup>2</sup>*  
43. (New) The semiconductor structure of claim 2, wherein the monocrystalline oxide is formed of material selected from the group consisting of  $\text{Sr}_z\text{Ba}_{1-z}\text{TiO}_3$ ,  $\text{Sr}_z\text{Ba}_{1-z}\text{ZrO}_3$ ,  $\text{Sr}_z\text{Ba}_{1-z}\text{HfO}_3$ ,  $\text{Sr}_z\text{Ba}_{1-z}\text{SnO}_3$  and  $\text{CaTiO}_3$ , where z ranges from 0 to approximately 1.

---

#### SUPPORT FOR THE AMENDMENTS

The amendment to Claim 1 places original Claim 16 in independent form, and thus places all pending claims in condition for allowance. The claim originally appearing at page 27, lines 18-20, has been presented as new Claim 43. No new matter has been entered.